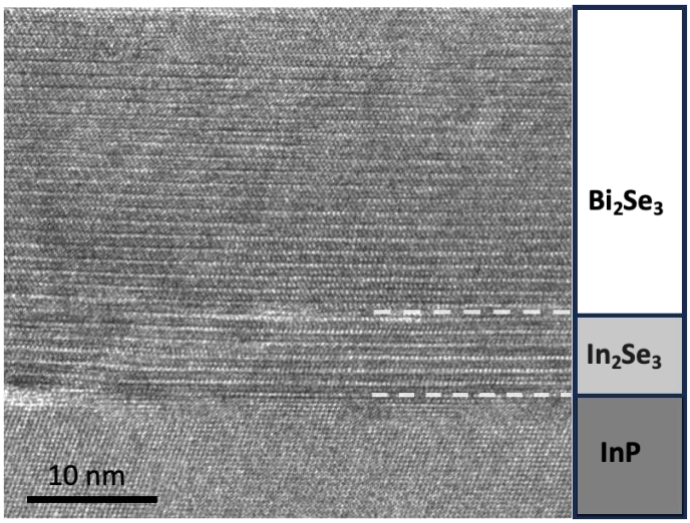

Figure 1. Cross-sectional HR-TEM image of Bi_2Se_3 on In_2Se_3 layer grown via selenium passivation of InP(111)B substrate showing abrupt interfaces between the layers.

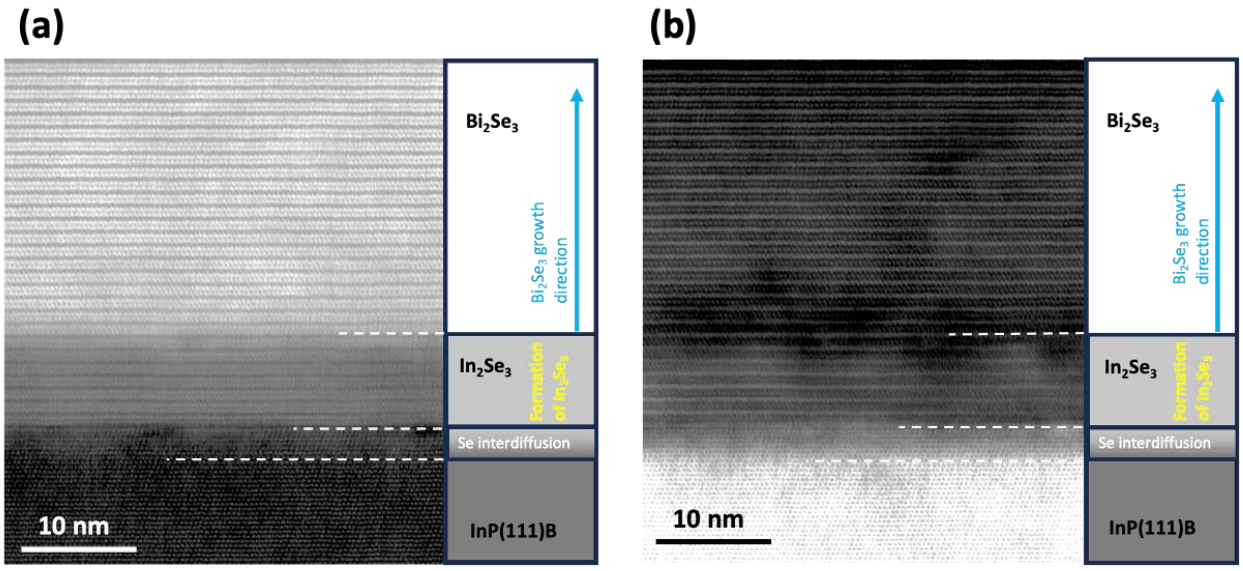

Figure 2. Cross-sectional (a)HAADF and (b) BF image of Bi_2Se_3 on In_2Se_3 layer grown via selenium passivation of InP(111)B substrate clearly showing abrupt interface between Bi_2Se_3 and In_2Se_3 layers and the zinc blende InP lattice and the rhombohedral In_2Se_3 layer. Images also show selenium diffusion further into the substrate without changing the crystal structure of zinc blende InP.